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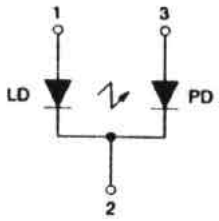
RLT7825G TECHNICAL DATA

Infrared Laserdiode

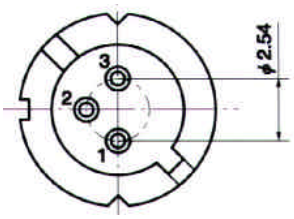
Structure: **GaAlAs, double heterostructure, index guided**
Lasing wavelength: **780 nm**
Max. optical power: **25 mW**
Package: **9 mm**

NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



1) Laser diode anode
2) Laser diode cathode and photodiode cathode
3) Photodiode anode



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	25	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operation Case Temperature	T_C	-10 .. +50	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I_{th}		-	50	70	mA
Operation Current	I_{op}	P_o = 20 mW	-	90	130	mA
Operating Voltage	V_{op}	P_o = 20 mW		2.2	2.5	V
Lasing Wavelength	λ_p	P_o = 20 mW	770	780	800	nm
Beam Divergence	$\theta_{//}$	P_o = 20 mW	7	11	15	°
Beam Divergence	$\theta_{\perp}$	P_o = 20 mW	15	28	40	°
Off Axis Angle	$\Delta\theta_{\perp}$	-	-	-	± 3	°
Off Axis Angle	$\Delta\theta_{//}$	-	-	-	± 3	°
Monitor Current	I_m	P_o = 20 mW	0.2	1.0	-	mA